

FIG. 1

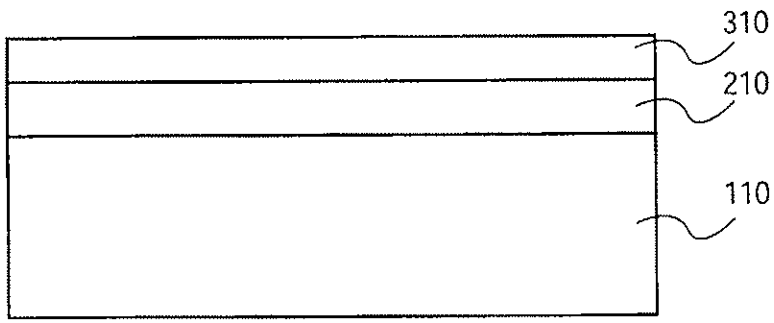


FIG. 2

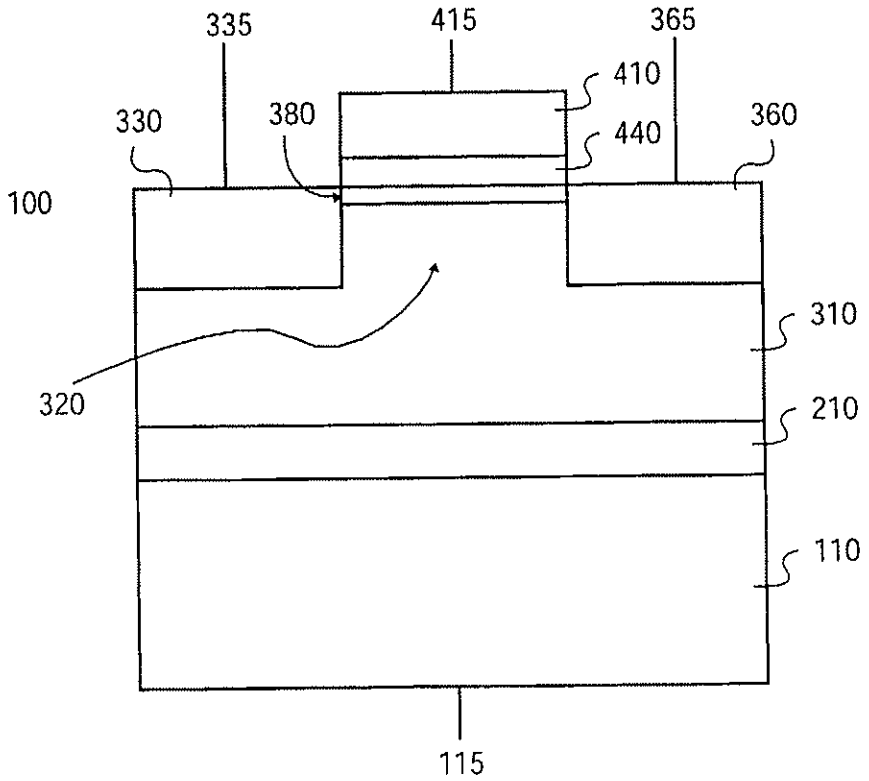


FIG. 3

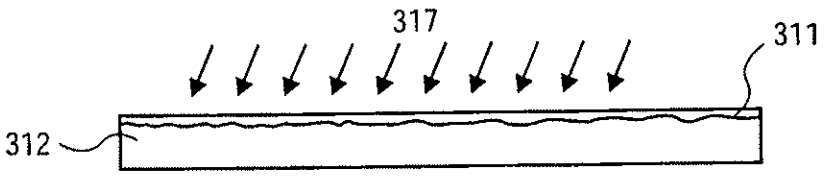


FIG. 4

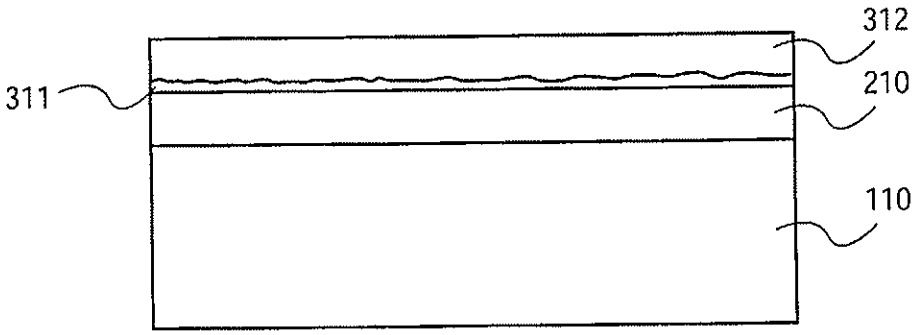


FIG. 5

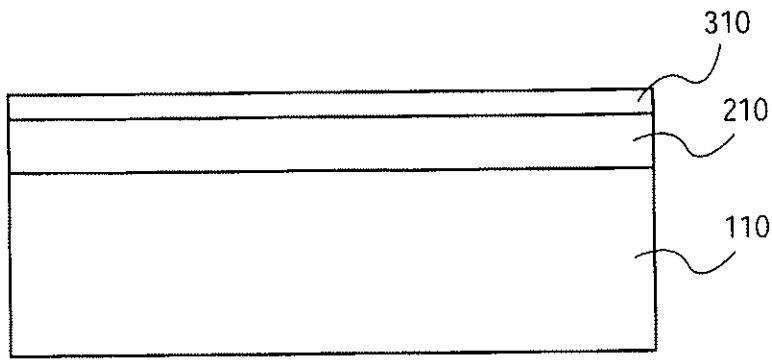


FIG. 6

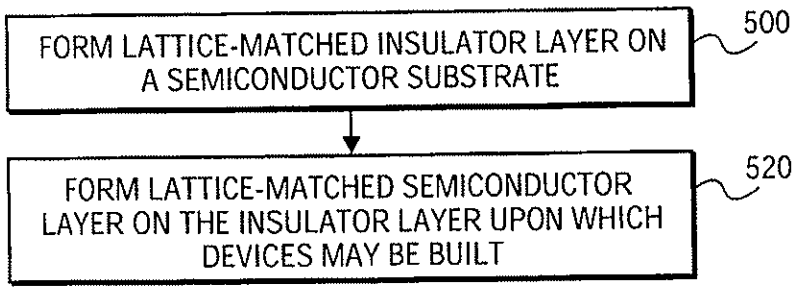

FORM LATTICE-MATCHED INSULATOR LAYER ON A SEMICONDUCTOR SUBSTRATE
500
FORM LATTICE-MATCHED SEMICONDUCTOR LAYER ON THE INSULATOR LAYER UPON WHICH DEVICES MAY BE BUILT
520

FIG. 7

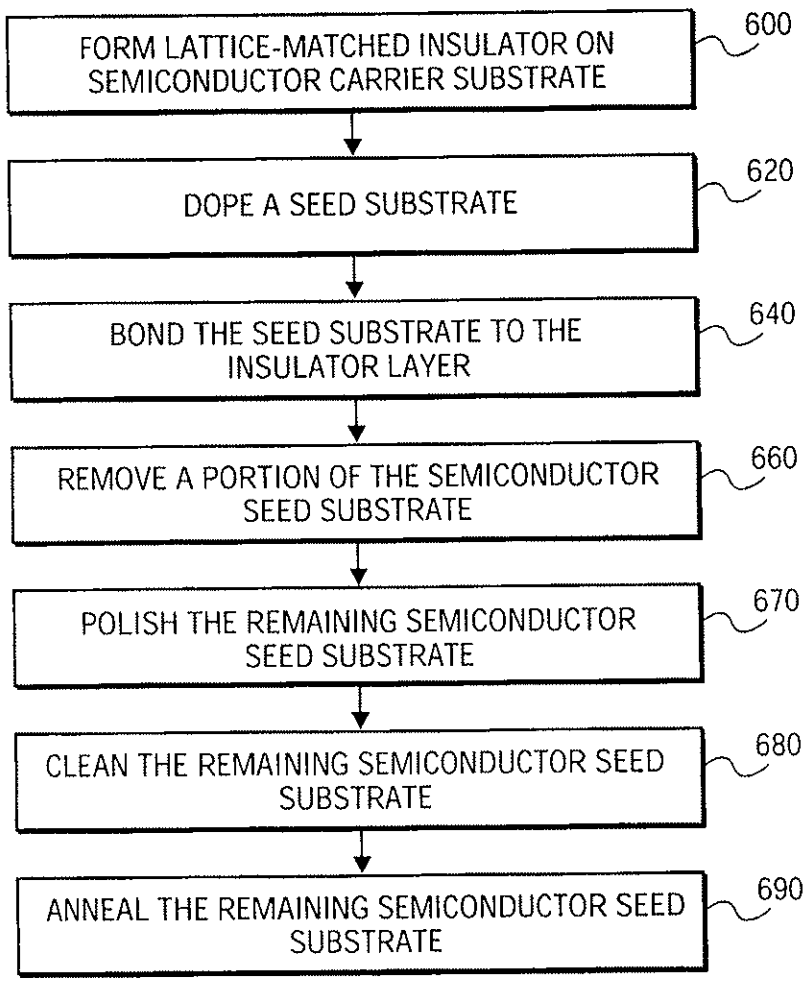

FORM LATTICE-MATCHED INSULATOR ON SEMICONDUCTOR CARRIER SUBSTRATE
600
DOPE A SEED SUBSTRATE
620
BOND THE SEED SUBSTRATE TO THE INSULATOR LAYER
640
REMOVE A PORTION OF THE SEMICONDUCTOR SEED SUBSTRATE
660
POLISH THE REMAINING SEMICONDUCTOR SEED SUBSTRATE
670
CLEAN THE REMAINING SEMICONDUCTOR SEED SUBSTRATE
680
ANNEAL THE REMAINING SEMICONDUCTOR SEED SUBSTRATE
690

FIG. 8

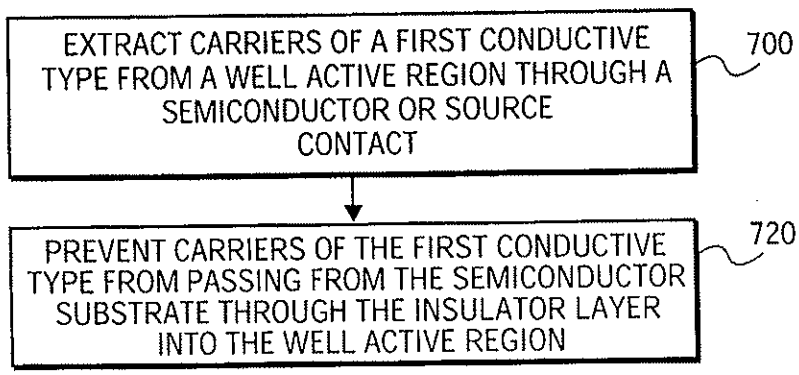

EXTRACT CARRIERS OF A FIRST CONDUCTIVE TYPE FROM A WELL ACTIVE REGION THROUGH A SEMICONDUCTOR OR SOURCE CONTACT
700
PREVENT CARRIERS OF THE FIRST CONDUCTIVE TYPE FROM PASSING FROM THE SEMICONDUCTOR SUBSTRATE THROUGH THE INSULATOR LAYER INTO THE WELL ACTIVE REGION
720

FIG. 9